

Amendments to the Claims

1. (Currently Amended): A boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition, comprising:

a carrier gas;

at least one of ~~C_4F_6 , C_3F_6~~ C_4F_6 and C_5F_8 ;

CH_2F_2 ; and

a gas selected from the group consisting of CHF_3 , CF_4 , and mixtures thereof constituting a boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition.

Claims 2 and 3 (Canceled).

4. (Original): The etchant gas composition according to Claim 1, wherein the carrier gas is selected from the group consisting of argon, helium, and xenon.

5. (Previously Presented): The etchant gas composition according to Claim 1, wherein the carrier gas comprises argon.

6. (Currently Amended): A boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition, consisting essentially of:

a carrier gas;

at least one of ~~C_4F_6 , C_3F_8~~ C_4F_6 and C_5F_8 ;

CH_2F_2 ; and

CHF_3 constituting a boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition.

Claims 7 and 8 (Canceled).

9. (Original): The etchant gas composition according to Claim 6, wherein the carrier gas is selected from the group consisting of argon, helium, and xenon.

10. (Previously Presented): The etchant gas composition according to Claim 6, wherein the carrier gas comprises argon.

11. (Currently Amended): A boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition, consisting essentially of:

a carrier gas;

at least one of ~~C_4F_6 , C_3F_8~~ , C_4F_6 and C_5F_8 ;

CH_2F_2 ; and

CF_4 constituting a boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition.

Claims 12 and 13 (Canceled).

14. (Original): The etchant gas composition according to Claim 11, wherein the carrier gas is selected from the group consisting of argon, helium, and xenon.

15. (Previously Presented): The etchant gas composition according to Claim 11, wherein the carrier gas comprises argon.

16. (Currently Amended): A boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition, consisting essentially of:

a carrier gas;

at least one of ~~C_4F_6 , C_3F_8~~ C_4F_6 and C_5F_8 ;

CH_2F_2 ;

CHF_3 ; and

CF_4 constituting a boron and/or phosphorus doped silicon dioxide selective to undoped SiO_2 and Si_3N_4 etchant gas composition.

Claims 17 and 18 (Canceled).

19. (Original): The etchant gas composition according to Claim 6, wherein the carrier gas is selected from the group consisting of argon, helium, and xenon.

20. (Previously Presented): The etchant gas composition according to Claim 16, wherein the carrier gas comprises argon.

Claims 21-64 (Canceled).

65. (Previously Presented): The etchant gas composition according to Claim 1 comprising O_2 .

66. (Previously Presented): The etchant gas composition according to Claim 1 comprising CO.

67. (Previously Presented): The etchant gas composition according to Claim 1 wherein the carrier gas comprises helium.

68. (Previously Presented): The etchant gas composition according to Claim 6 wherein the carrier gas comprises helium.

69. (Previously Presented): The etchant gas composition according to Claim 11 wherein the carrier gas comprises helium.

70. (Previously Presented): The etchant gas composition according to Claim 16 wherein the carrier gas comprises helium.

71. (Previously Presented): The etchant gas composition according to Claim 1 wherein the carrier gas comprises xenon.

72. (Previously Presented): The etchant gas composition according to Claim 6 wherein the carrier gas comprises xenon.

73. (Previously Presented): The etchant gas composition according to Claim 11 wherein the carrier gas comprises xenon.

74. (Previously Presented): The etchant gas composition according to Claim 16 wherein the carrier gas comprises xenon.

75. (Previously Presented): The etchant gas composition according to Claim 1, comprising C_4F_6 .

Claim 76 (Canceled).

77. (Previously Presented): The etchant gas composition according to Claim 1, comprising C_5F_8 .

78. (Previously Presented): The etchant gas composition according to Claim 6, comprising C_4F_6 .

Claim 79 (Canceled).

80. (Previously Presented): The etchant gas composition according to Claim 6, comprising C_5F_8 .

81. (Previously Presented): The etchant gas composition according to Claim 11, comprising C_4F_6 .

Claim 82 (Canceled).

83. (Previously Presented): The etchant gas composition according to Claim 11, comprising C_5F_8 .

84. (Previously Presented): The etchant gas composition according to Claim 16, comprising C_4F_6 .

Claim 85 (Canceled).

86. (Previously Presented): The etchant gas composition according to Claim 16, comprising C_5F_8 .